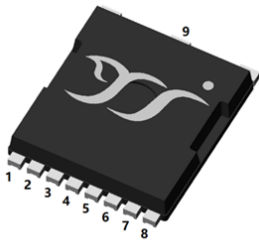
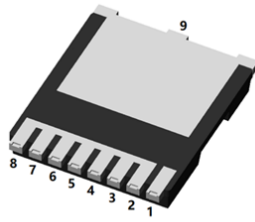


## N-Channel Enhancement Mode Field Effect Transistor

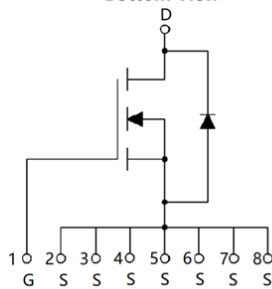


Top View



Bottom View

**TOLL**



### Product Summary

- $V_{DS}$  40V
- $I_D$  225A
- $R_{DS(ON)}$  (at  $V_{GS}=10V$ )  $< 1.2m\Omega$
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free
- Part no. with suffix "Q" means AEC-Q101 qualified

### Applications

- High power inverter system
- Uninterruptible power supply
- LCDM appliances

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	40	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25^\circ C$	$I_D$	25	A
	$T_A=100^\circ C$		17.8	
	$T_C=25^\circ C$		225	
	$T_C=100^\circ C$		159	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	400	A
Avalanche energy <sup>B</sup>		EAS	1441	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25^\circ C$	$P_D$	2	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		166	
	$T_C=100^\circ C$		83	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+175	$^\circ C$

### ■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	$R_{\theta JA}$	60	72	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.75	0.9	

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJT225G04HJQ	F1	YJT225G04HJ	2000	4000	20000	13" reel

■ Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=1mA$	2	2.5	3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=75A$	-	0.9	1.2	m $\Omega$
Diode Forward Voltage	$V_{SD}$	$I_S=20A, V_{GS}=0V$	-	0.75	1.2	V
Gate resistance	$R_G$	$f=1MHz$	-	3	-	$\Omega$
Maximum Body-Diode Continuous Current	$I_S$		-	-	225	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	-	6830	-	pF
Output Capacitance	$C_{oss}$		-	1970	-	
Reverse Transfer Capacitance	$C_{rss}$		-	148	-	
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{GS}=10V, V_{DS}=20V, I_D=50A$	-	84.3	-	nC
Gate-Source Charge	$Q_{gs}$		-	30	-	
Gate-Drain Charge	$Q_{gd}$		-	11.46	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=50A, di/dt=100A/us$	-	63	-	nC
Reverse Recovery Time	$t_{rr}$		-	58	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=20V, I_D=50A$ $R_{GEN}=2.5\Omega$	-	18	-	ns
Turn-on Rise Time	$t_r$		-	13	-	
Turn-off Delay Time	$t_{D(off)}$		-	58	-	
Turn-off fall Time	$t_f$		-	28	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B.  $T_J=25^\circ\text{C}$ ,  $V_{DD}=100V$ ,  $V_G=10V$ ,  $L=3mH$ ,  $I_{AS}=31A$ .

C.  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.

D. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with  $T_A=25^\circ\text{C}$ . The maximum allowed junction temperature of  $175^\circ\text{C}$ . The value in any given application depends on the user's specific board design.



## Typical Electrical and Thermal Characteristics Diagrams

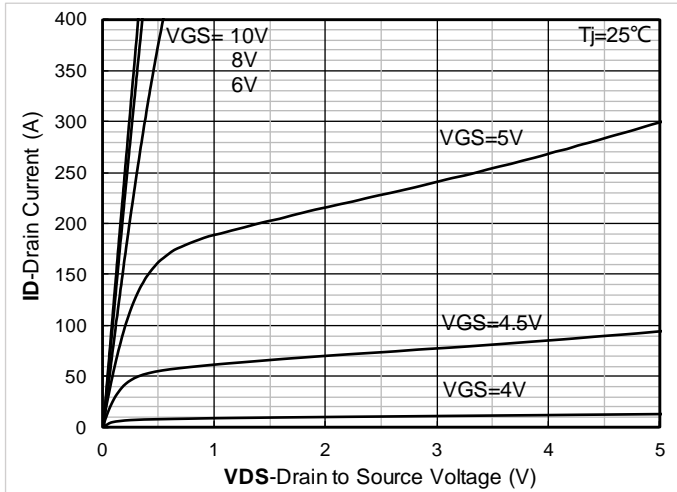


Figure 1. Output Characteristics

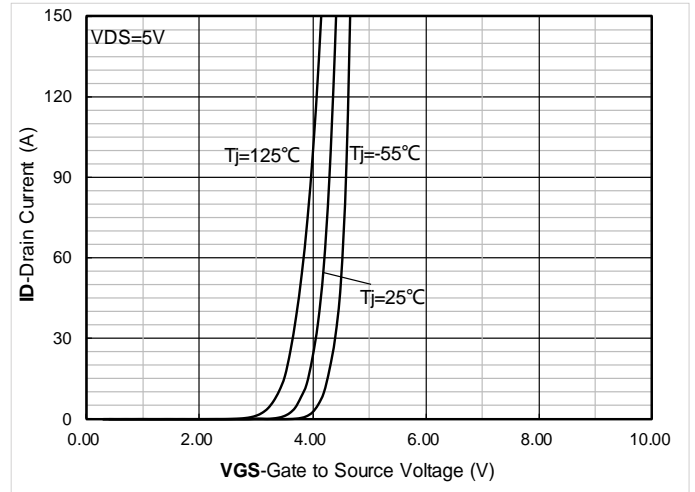


Figure 2. Transfer Characteristics

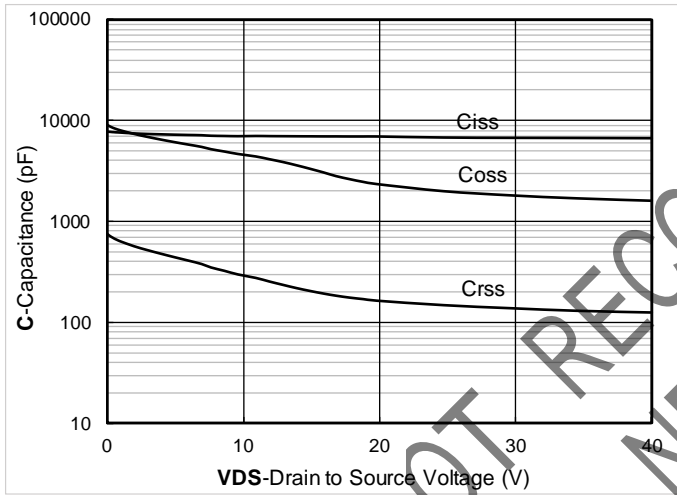


Figure 3. Capacitance Characteristics

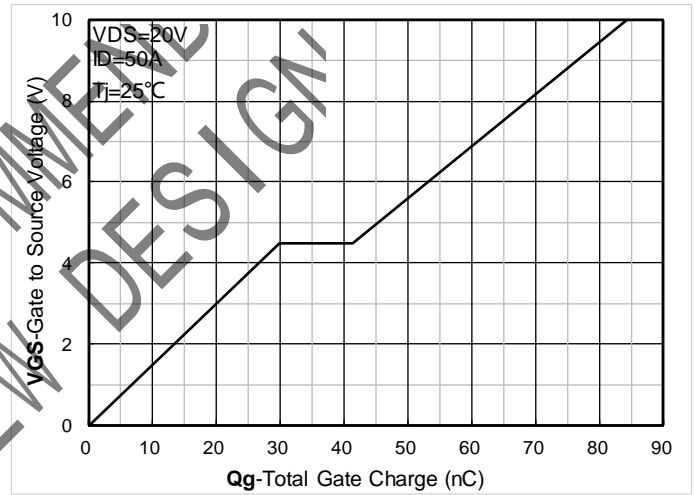


Figure 4. Gate Charge

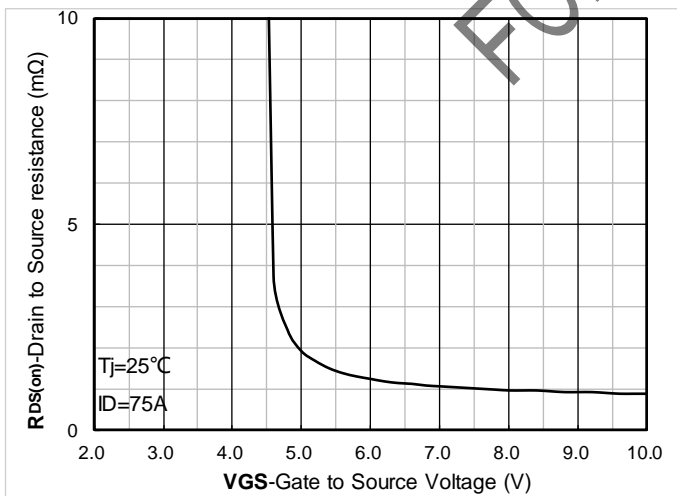


Figure 5. On-Resistance vs Gate to Source Voltage

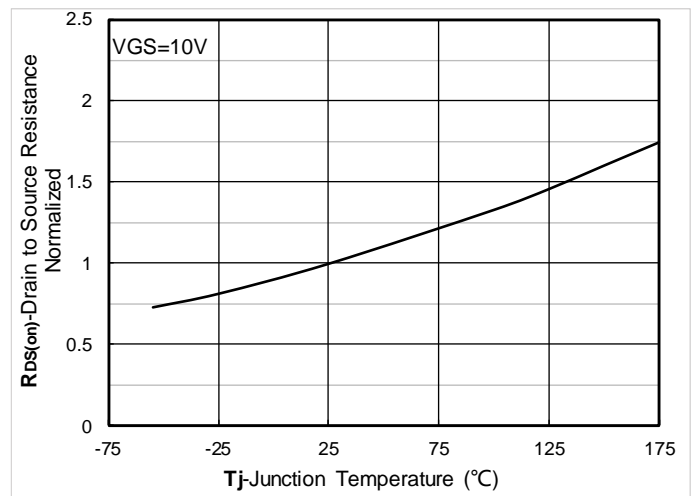


Figure 6. Normalized On-Resistance

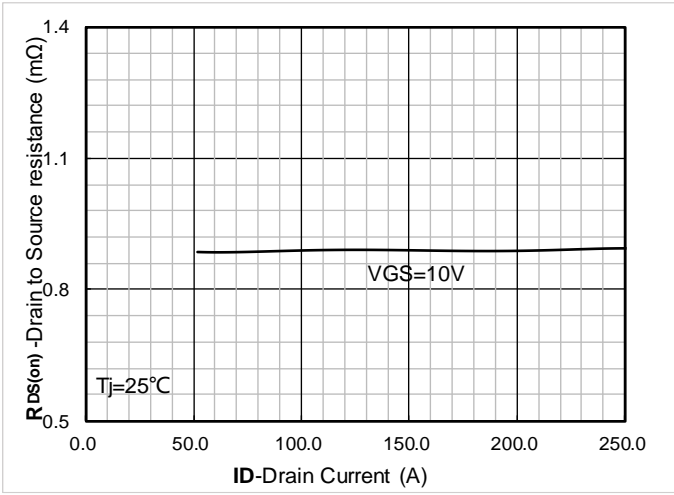


Figure 7.  $R_{DS(on)}$  VS Drain Current

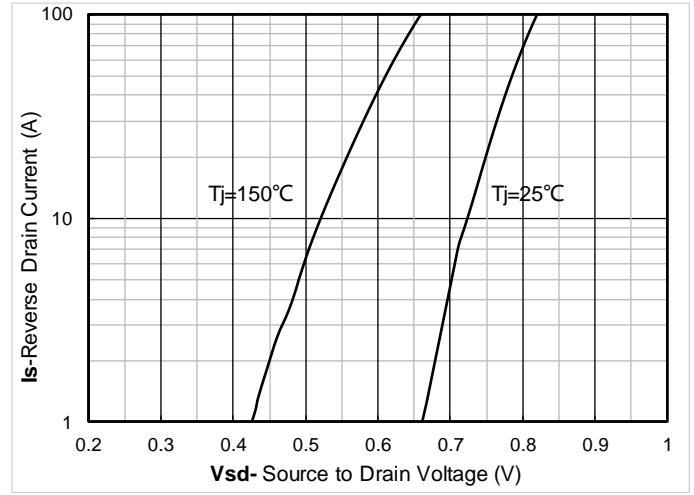


Figure 8. Forward characteristics of reverse diode

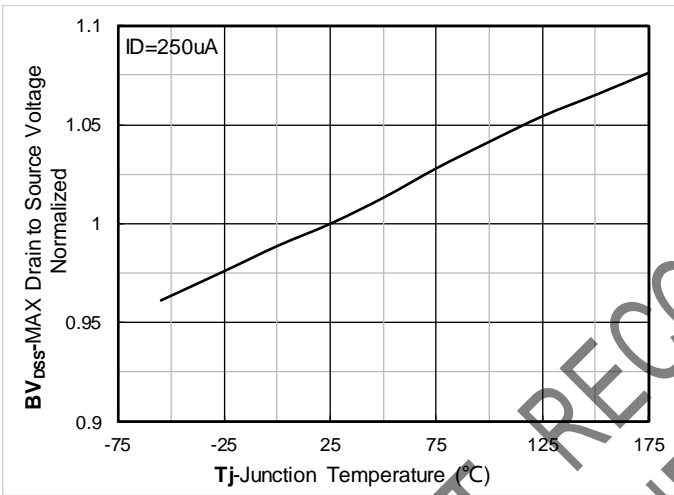


Figure 9. Normalized breakdown voltage

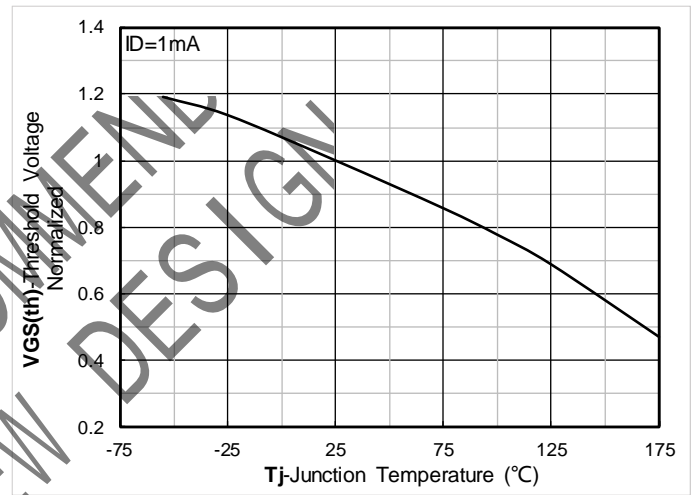


Figure 10. Normalized Threshold voltage

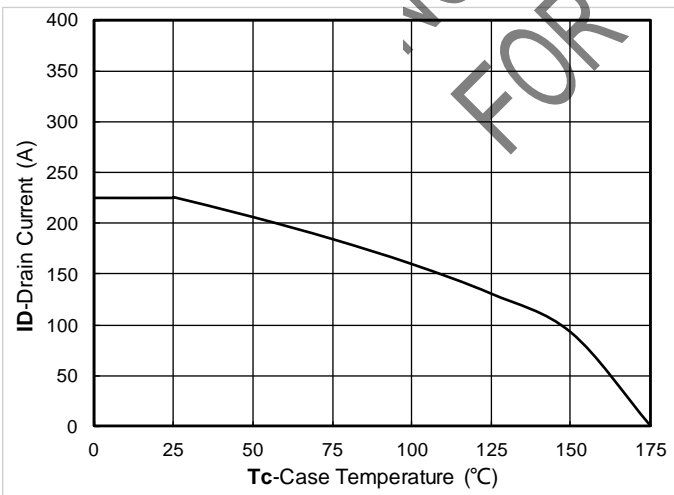


Figure 11. Current dissipation

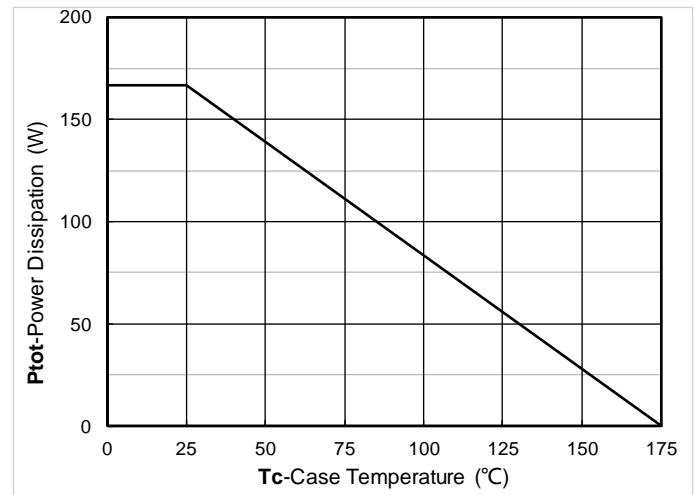


Figure 12. Power dissipation

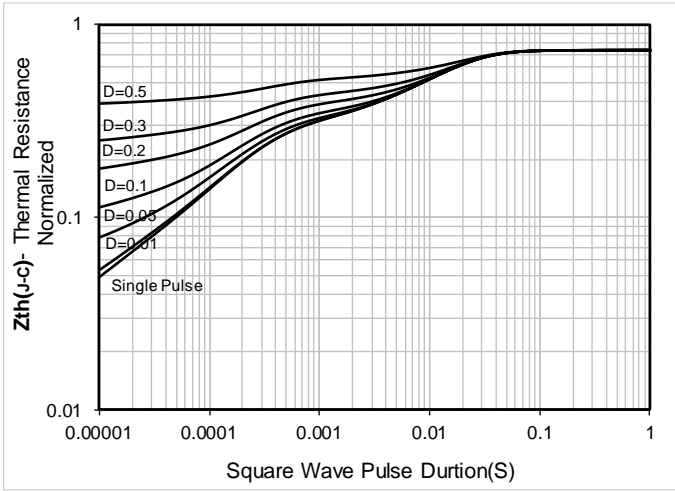


Figure 13. Maximum Transient Thermal Impedance

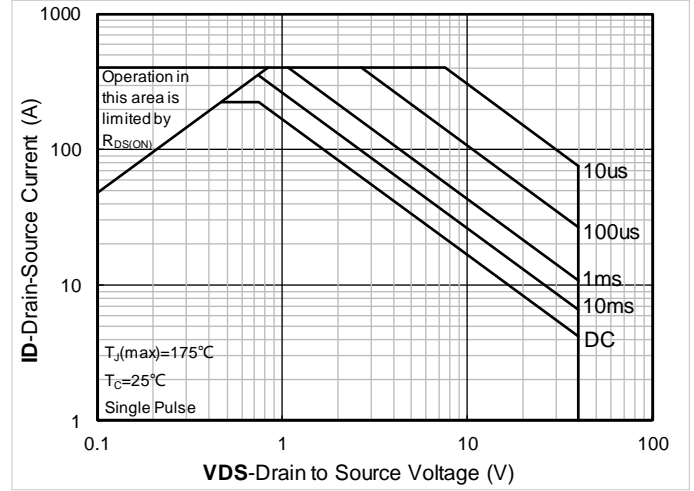


Figure 14. Safe Operation Area

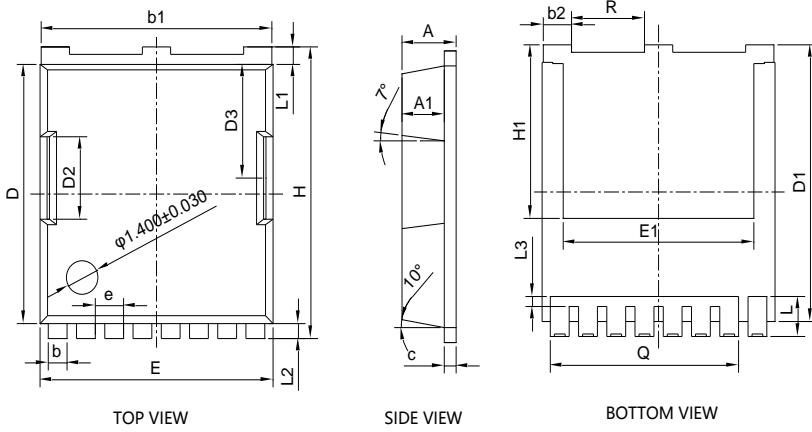
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FOR NEW DESIGN



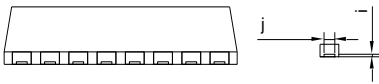
# YJT225G04HJQ

RECOMMEND  
YJT1D3G04HQ  
FOR NEW DESIGN

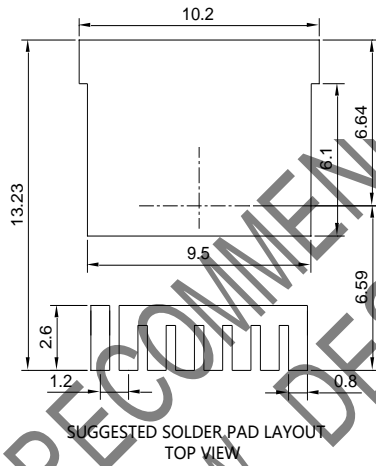
## ■ TOLL Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.2	2.3	2.4
A1	1.7	1.8	1.9
b	0.7	0.8	0.9
b1	9.7	9.8	9.9
b2	1.1	1.2	1.3
c	0.4	0.5	0.6
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.2	3.3	3.4
D3	4.45	4.55	4.65
E	9.8	9.9	10
E1	8	8.1	8.2
e	1.2 BSC		
H	11.58	11.68	11.78
H1	6.95 BSC		
i	0.1 REF		
j	0.46 REF		
L	1.5	1.6	1.7
L1	0.6	0.7	0.8
L2	0.5	0.6	0.7
L3	0.3	0.4	0.5
Q	8 REF		
R	3.0	3.1	3.2



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.03\text{mm}$ .
  3. The pad layout is for reference purposes only.



UNIT: mm

NOT RECOMMEND FOR NEW DESIGN



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